



# TSB75T080S(A)S-255A

5A/80V, low VF Schottky barrier diode with trench MOS structure

## Mechanical Data

Chip Drawing	Item	Information	
	Die Size (A)	1905 $\mu\text{m}$	75 mil
	Top Metal Pad Size (B)	1812 $\mu\text{m}$	71mil
	Chip Size (C)	1825 $\mu\text{m}$	72mil
	Wafer Thickness (D)	255 $\mu\text{m}$	9.5 mil
	Scribe Line Width (E)	80 $\mu\text{m}$	3.15 mil
	Wafer Size	6 inch	
	Top Side Metallization	TSB75T080SS-255A	Al/Ag
	Back Side Metallization	Ti Ni Ag	
	Recommended Storage Environment	Stored in original container, in dry nitrogen, (6 months at an ambient temperature of 23 $\pm$ 3 )	

## Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise specified)<sup>(1)</sup>

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V <sub>BR</sub>	Reverse Breakdown Voltage	85	92	-	V	I <sub>R</sub> =100 $\mu\text{A}$
V <sub>F</sub>	Instantaneous Forward Voltage	-	0.52	0.54	V	I <sub>F</sub> =5A <sup>(3)</sup>
I <sub>R</sub>	Reverse Leakage Current	-	8	40		V <sub>R</sub> =80V
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-40				